

# Wladyslaw

## List of Publications by Citations

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444  
papers

20,373  
citations

69  
h-index

130  
g-index

475  
ext. papers

21,779  
ext. citations

3.3  
avg, IF

6.35  
L-index

#	Paper	IF	Citations
444	Band Anticrossing in GaInNAs Alloys. <i>Physical Review Letters</i> , <b>1999</b> , 82, 1221-1224	7.4	1359
443	Unusual properties of the fundamental band gap of InN. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 3967-3969	3.4	1254
442	Superior radiation resistance of In <sub>1-x</sub> Ga <sub>x</sub> N alloys: Full-solar-spectrum photovoltaic material system. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 6477-6482	2.5	503
441	Small band gap bowing in In <sub>1-x</sub> Ga <sub>x</sub> N alloys. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 4741-4743	3.4	498
440	Effect of the location of Mn sites in ferromagnetic Ga <sub>1-x</sub> Mn <sub>x</sub> As on its Curie temperature. <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	461
439	Electron mobility in modulation-doped heterostructures. <i>Physical Review B</i> , <b>1984</b> , 30, 4571-4582	3.3	402
438	Effects of the narrow band gap on the properties of InN. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	346
437	Temperature dependence of the fundamental band gap of InN. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 4457-4460	3.37	337
436	Valence-band anticrossing in mismatched III-V semiconductor alloys. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	310
435	Intrinsic limitations to the doping of wide-gap semiconductors. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 302-303, 123-134	2.8	279
434	Origin of the 0.82-eV electron trap in GaAs and its annihilation by shallow donors. <i>Applied Physics Letters</i> , <b>1982</b> , 40, 342-344	3.4	264
433	Valence band anticrossing in GaBi <sub>x</sub> As <sub>1-x</sub> . <i>Applied Physics Letters</i> , <b>2007</b> , 91, 051909	3.4	262
432	Band anticrossing in highly mismatched IIIIV semiconductor alloys. <i>Semiconductor Science and Technology</i> , <b>2002</b> , 17, 860-869	1.8	262
431	Amphoteric native defects in semiconductors. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 2094-2096	3.4	242
430	Electron mobility and free-carrier absorption in InP; determination of the compensation ratio. <i>Journal of Applied Physics</i> , <b>1980</b> , 51, 2659	2.5	242
429	Nature of room-temperature photoluminescence in ZnO. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 191911	3.4	237
428	Electron mobility and free-carrier absorption in GaAs: Determination of the compensation ratio. <i>Journal of Applied Physics</i> , <b>1979</b> , 50, 899-908	2.5	229

427	Engineering the electronic band structure for multiband solar cells. <i>Physical Review Letters</i> , <b>2011</b> , 106, 028701	7.4	225
426	Diluted II-VI oxide semiconductors with multiple band gaps. <i>Physical Review Letters</i> , <b>2003</b> , 91, 246403	7.4	219
425	Native point defects in low-temperature-grown GaAs. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 279-281	3.4	217
424	Large, nitrogen-induced increase of the electron effective mass in In <sub>y</sub> Ga <sub>1-y</sub> N <sub>x</sub> As <sub>1-x</sub> . <i>Applied Physics Letters</i> , <b>2000</b> , 76, 2409-2411	3.4	212
423	Structure and electronic properties of InN and In-rich group III-nitride alloys. <i>Journal Physics D: Applied Physics</i> , <b>2006</b> , 39, R83-R99	3	211
422	Nature of the fundamental band gap in GaN <sub>x</sub> P <sub>1-x</sub> alloys. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 3251-3253	3.4	211
421	Effects of electron concentration on the optical absorption edge of InN. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 2805-2807	3.4	210
420	Electron mobility in Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructures. <i>Physical Review B</i> , <b>1997</b> , 56, 1520-1528	3.3	185
419	Evidence for p-type doping of InN. <i>Physical Review Letters</i> , <b>2006</b> , 96, 125505	7.4	176
418	Raman Spectroscopy and Time-Resolved Photoluminescence of BN and B <sub>x</sub> C <sub>y</sub> N <sub>z</sub> Nanotubes. <i>Nano Letters</i> , <b>2004</b> , 4, 647-650	11.5	175
417	Fermi-level stabilization energy in group III nitrides. <i>Physical Review B</i> , <b>2005</b> , 71,	3.3	172
416	Interaction of localized electronic states with the conduction band: band anticrossing in II-VI semiconductor ternaries. <i>Physical Review Letters</i> , <b>2000</b> , 85, 1552-5	7.4	162
415	Fano interference of the Raman phonon in heavily boron-doped diamond films grown by chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 616-618	3.4	161
414	Controlling the Curie temperature in (Ga,Mn)As through location of the Fermi level within the impurity band. <i>Nature Materials</i> , <b>2012</b> , 11, 444-9	27	148
413	Band-edge hydrostatic deformation potentials in III-V semiconductors. <i>Physical Review Letters</i> , <b>1987</b> , 59, 501-504	7.4	148
412	Finite element simulations of compositionally graded InGaN solar cells. <i>Solar Energy Materials and Solar Cells</i> , <b>2010</b> , 94, 478-483	6.4	145
411	Optical properties and electronic structure of InN and In-rich group III-nitride alloys. <i>Journal of Crystal Growth</i> , <b>2004</b> , 269, 119-127	1.6	145
410	Metastability of Oxygen Donors in AlGaN. <i>Physical Review Letters</i> , <b>1998</b> , 80, 4008-4011	7.4	138

409	Band gaps of InN and group III nitride alloys. <i>Superlattices and Microstructures</i> , <b>2003</b> , 34, 63-75	2.8	137
408	Mechanism of Fermi-level stabilization in semiconductors. <i>Physical Review B</i> , <b>1988</b> , 37, 4760-4763	3.3	135
407	Persistent photoconductivity in n-type GaN. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 1098-1100	3.4	133
406	Effect of nitrogen on the band structure of GaInNAs alloys. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 2349-2355	3.5	130
405	Optical properties of In <sub>x</sub> Ga <sub>1-x</sub> N alloys grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 4452-4458	2.5	127
404	Modeling of InGaN/Si tandem solar cells. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 024507	2.5	126
403	Effect of polarization fields on transport properties in AlGa <sub>x</sub> N/GaN heterostructures. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 1783	2.5	119
402	Multiband GaNAsP quaternary alloys. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 092110	3.4	112
401	Band Anticrossing in III-V Alloys. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 223, 75-85	1.3	107
400	Role of nitrogen in the reduced temperature dependence of band-gap energy in GaNAs. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 3021-3023	3.4	105
399	Dependence of the fundamental band gap of Al <sub>x</sub> Ga <sub>1-x</sub> N on alloy composition and pressure. <i>Journal of Applied Physics</i> , <b>1999</b> , 85, 8505-8507	2.5	100
398	Annealing studies of low-temperature-grown GaAs:Be. <i>Journal of Applied Physics</i> , <b>1992</b> , 71, 1699-1707	2.5	98
397	On the crystalline structure, stoichiometry and band gap of InN thin films. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 071910	3.4	97
396	Mechanism of Schottky barrier formation: The role of amphoteric native defects. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1987</b> , 5, 1062		96
395	Universal bandgap bowing in group-III nitride alloys. <i>Solid State Communications</i> , <b>2003</b> , 127, 411-414	1.6	92
394	Large disparity between gallium and antimony self-diffusion in gallium antimonide. <i>Nature</i> , <b>2000</b> , 408, 69-72	50.4	90
393	Reduction of band-gap energy in GaNAs and AlGa <sub>x</sub> NAs synthesized by N <sup>+</sup> implantation. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 1410-1412	3.4	90
392	Effect of nitrogen on the electronic band structure of group III-N-V alloys. <i>Physical Review B</i> , <b>2000</b> , 62, 4211-4214	3.3	89

391	Reconfiguring crystal and electronic structures of MoS by substitutional doping. <i>Nature Communications</i> , <b>2018</b> , 9, 199	17.4	85
390	Fermi level dependent native defect formation: Consequences for metal-semiconductor and semiconductor-semiconductor interfaces. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1988</b> , 6, 1257		85
389	Two-photon excitation in an intermediate band solar cell structure. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 172111	3.4	83
388	Curie temperature limit in ferromagnetic Ga <sub>1-x</sub> MnxAs. <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	83
387	Minority-carrier mobility in p-type GaAs. <i>Journal of Applied Physics</i> , <b>1979</b> , 50, 5040-5042	2.5	83
386	Pressure-dependent photoluminescence study of ZnO nanowires. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 1531-1534	3.7	80
385	Growth of a-plane InN on r-plane sapphire with a GaN buffer by molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1136-1138	3.4	80
384	Effect of band anticrossing on the optical transitions in GaAs <sub>1-x</sub> Nx/GaAs multiple quantum wells. <i>Physical Review B</i> , <b>2001</b> , 64,	3.3	80
383	Electron mobility in n-type GaAs at 77 K: Determination of the compensation ratio. <i>Journal of Applied Physics</i> , <b>1982</b> , 53, 769-770	2.5	80
382	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi <sub>2</sub> Te <sub>3</sub> by Multifunctionality of Native Defects. <i>Advanced Materials</i> , <b>2015</b> , 27, 3681-6	24	79
381	Valence band hybridization in N-rich GaN <sub>1-x</sub> Asx alloys. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	76
380	Existence and removal of Cu <sub>2</sub> Se second phase in coevaporated Cu <sub>2</sub> ZnSnSe <sub>4</sub> thin films. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 053522	2.5	74
379	Local-vibrational-mode spectroscopy of DX centers in Si-doped GaAs under hydrostatic pressure. <i>Physical Review Letters</i> , <b>1991</b> , 66, 774-777	7.4	74
378	Carrier localization of as-grown n-type gallium nitride under large hydrostatic pressure. <i>Physical Review B</i> , <b>1996</b> , 53, 1322-1326	3.3	71
377	Effect of oxygen on the electronic band structure in ZnOxSe <sub>1-x</sub> alloys. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 299-301	3.4	70
376	Ideal transparent conductors for full spectrum photovoltaics. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 123505	5	69
375	Enhancement of Curie temperature in Ga <sub>1-x</sub> MnxAs/Ga <sub>1-y</sub> AlyAs ferromagnetic heterostructures by Be modulation doping. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4220-4222	3.4	67
374	In <sub>1-x</sub> MnxSb <sub>x</sub> narrow-gap ferromagnetic semiconductor. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 4310-4312	3.4	67

373	Hydrostatic pressure dependence of the fundamental bandgap of InN and In-rich group III nitride alloys. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4963-4965	3.4	63
372	Hole transport and photoluminescence in Mg-doped InN. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 113712	2.5	62
371	Band gap bowing parameter of In <sub>1-x</sub> Al <sub>x</sub> N. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 123501	2.5	62
370	Band anticrossing in GaP <sub>1-x</sub> N <sub>x</sub> alloys. <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	62
369	Interband optical absorption in free standing layer of Ga <sub>0.96</sub> In <sub>0.04</sub> As <sub>0.99</sub> N <sub>0.01</sub> . <i>Applied Physics Letters</i> , <b>2000</b> , 76, 1279-1281	3.4	62
368	Origin of the large band-gap bowing in highly mismatched semiconductor alloys. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	61
367	Band structure of highly mismatched semiconductor alloys: Coherent potential approximation. <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	61
366	Electronic Band Structure of Ga <sub>x</sub> PyAs <sub>1-x</sub> Highly Mismatched Alloys: Suitability for Intermediate-Band Solar Cells. <i>Physical Review Applied</i> , <b>2014</b> , 1,	4.3	60
365	Nitrogen-induced increase of the maximum electron concentration in group III-N-V alloys. <i>Physical Review B</i> , <b>2000</b> , 61, R13337-R13340	3.3	60
364	Germanium <sup>70</sup> Ge/ <sup>74</sup> Ge isotope heterostructures: An approach to self-diffusion studies. <i>Physical Review B</i> , <b>1995</b> , 51, 16817-16821	3.3	60
363	Band anticrossing in highly mismatched Sn <sub>x</sub> Ge <sub>1-x</sub> semiconducting alloys. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	59
362	Effects of quantum confinement on the doping limit of semiconductor nanowires. <i>Nano Letters</i> , <b>2007</b> , 7, 1186-90	11.5	59
361	Pressure dependence of the fundamental band-gap energy of CdSe. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 67-69	3.4	58
360	Band structure and optical properties of In <sub>y</sub> Ga <sub>1-y</sub> As <sub>1-x</sub> N <sub>x</sub> alloys. <i>Physical Review B</i> , <b>2001</b> , 65,	3.3	58
359	Carrier scattering by native defects in heavily doped semiconductors. <i>Physical Review B</i> , <b>1990</b> , 41, 102183-102205	3.1	58
358	Effects of surface states on electrical characteristics of InN and In <sub>1-x</sub> Ga <sub>x</sub> N. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	57
357	Current status of research and development of III <sup>+</sup> N <sup>-</sup> IV semiconductor alloys. <i>Semiconductor Science and Technology</i> , <b>2002</b> , 17, 741-745	1.8	57
356	Phosphorus antisite defects in low-temperature InP. <i>Physical Review B</i> , <b>1993</b> , 47, 4111-4114	3.3	57

355	Synthesis and optical properties of II-O-VI highly mismatched alloys. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 6232-6238	2.5	55
354	Fermi level stabilization energy in cadmium oxide. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 113706	2.5	54
353	Highly mismatched crystalline and amorphous GaN <sub>1-x</sub> As <sub>x</sub> alloys in the whole composition range. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 103709	2.5	54
352	Demonstration of a III-Nitride/Silicon Tandem Solar Cell. <i>Applied Physics Express</i> , <b>2009</b> , 2, 122202	2.4	54
351	Mg-doped InN and InGaN [Photoluminescence, capacitance]oltage and thermopower measurements. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 873-877	1.3	53
350	Crystal structure and properties of Cd <sub>x</sub> Zn <sub>1-x</sub> O alloys across the full composition range. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 232103	3.4	52
349	High quality InN/GaN heterostructures grown by migration enhanced metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 1892-1894	3.4	52
348	Mutual passivation of electrically active and isovalent impurities. <i>Nature Materials</i> , <b>2002</b> , 1, 185-9	2.7	51
347	Effects of piezoelectric field on defect formation, charge transfer, and electron transport at GaN/Al <sub>x</sub> Ga <sub>1-x</sub> N interfaces. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 339-341	3.4	51
346	Molecular beam epitaxial growth and optical properties of highly mismatched ZnTe <sub>1-x</sub> O <sub>x</sub> alloys. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 011905	3.4	50
345	Photocurrent induced by two-photon excitation in ZnTeO intermediate band solar cells. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 052111	3.4	50
344	Band structure engineering of ZnO <sub>1-x</sub> Se <sub>x</sub> alloys. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 022104	3.4	50
343	Defect formation and diffusion in heavily doped semiconductors. <i>Physical Review B</i> , <b>1994</b> , 50, 5221-5225	3.3	48
342	Electron mobility in InN and III-N alloys. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 073705	2.5	46
341	Structure-Dependent Hydrostatic Deformation Potentials of Individual Single-Walled Carbon Nanotubes. <i>Physical Review Letters</i> , <b>2004</b> , 93,	7.4	46
340	Acoustic phonon scattering of two-dimensional electrons in GaN/AlGa <sub>N</sub> heterostructures. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 1228-1230	3.4	46
339	Arsenic antisite-related defects in low-temperature MBE grown GaAs. <i>Semiconductor Science and Technology</i> , <b>1992</b> , 7, 1037-1041	1.8	45
338	Determination of free hole concentration in ferromagnetic Ga <sub>1-x</sub> Mn <sub>x</sub> As using electrochemical capacitance]oltage profiling. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 844-846	3.4	44

337	Electronic structure of Ga <sub>1-x</sub> Mn <sub>x</sub> As analyzed according to hole-concentration-dependent measurements. <i>Physical Review B</i> , <b>2010</b> , 81,	3-3	43
336	Synthesis of Ga <sub>N</sub> As <sub>1-x</sub> thin films by pulsed laser melting and rapid thermal annealing of N <sup>+</sup> -implanted GaAs. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 1043-1049	2-5	43
335	Structural and electronic properties of amorphous and polycrystalline In <sub>2</sub> Se <sub>3</sub> films. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 2390-2397	2-5	42
334	Mg doped InN and confirmation of free holes in InN. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 042104	3-4	41
333	Formation of Mn-derived impurity band in III-Mn-V alloys by valence band anticrossing. <i>Physical Review B</i> , <b>2008</b> , 78,	3-3	41
332	Compensating point defects in He <sup>+</sup> -irradiated InN. <i>Physical Review B</i> , <b>2007</b> , 75,	3-3	41
331	Effects of Free Carriers on the Optical Properties of Doped CdO for Full-Spectrum Photovoltaics. <i>Physical Review Applied</i> , <b>2016</b> , 6,	4-3	41
330	Fermi-level stabilization in the topological insulators Bi <sub>2</sub> Se <sub>3</sub> and Bi <sub>2</sub> Te <sub>3</sub> : Origin of the surface electron gas. <i>Physical Review B</i> , <b>2014</b> , 89,	3-3	39
329	Synthesis of In <sub>N</sub> P <sub>1-x</sub> thin films by N ion implantation. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 1077-1079	3-4	39
328	Formation of diluted III <sub>N</sub> nitride thin films by N ion implantation. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 2227-2234	2-5	37
327	Growth and characterization of ZnO <sub>1-x</sub> S <sub>x</sub> highly mismatched alloys over the entire composition. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 215702	2-5	36
326	Full multiple scattering analysis of XANES at the Cd L <sub>3</sub> and O K edges in CdO films combined with a soft-x-ray emission investigation. <i>Physical Review B</i> , <b>2010</b> , 82,	3-3	36
325	Effects of point defects on thermal and thermoelectric properties of InN. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 012108	3-4	36
324	Theoretical transport studies of p-type GaN/AlGa <sub>N</sub> modulation-doped heterostructures. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 2405-2407	3-4	36
323	Electron cyclotron effective mass in indium nitride. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 052117	3-4	35
322	Mechanisms of Schottky Barrier Control on n-Type Germanium Using Ge <sub>3</sub> N <sub>4</sub> Interlayers. <i>Journal of the Electrochemical Society</i> , <b>2011</b> , 158, H358	3-9	35
321	Band-gap bowing effects in B <sub>x</sub> Ga <sub>1-x</sub> As alloys. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 2696-2699	2-5	35
320	Transport-to-quantum lifetime ratios in AlGa <sub>N</sub> /Ga <sub>N</sub> heterostructures. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 2508-2510	3-4	34

3 <sup>19</sup>	Pressure dependence of Schottky barrier height at the Pt/GaAs interface. <i>Applied Physics Letters</i> , <b>1988</b> , 53, 974-976	3-4	34
3 <sup>18</sup>	Shallow donor associated with the main electron trap (EL2) in melt-grown GaAs. <i>Applied Physics Letters</i> , <b>1983</b> , 43, 112-114	3-4	34
3 <sup>17</sup>	Demonstration of homojunction ZnTe solar cells. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 024502	2.5	33
3 <sup>16</sup>	Determination of effective mass in InN by high-field oscillatory magnetoabsorption spectroscopy. <i>Physical Review B</i> , <b>2011</b> , 83,	3-3	33
3 <sup>15</sup>	Growth and properties of ferromagnetic In <sub>1-x</sub> MnxSb alloys. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 20, 325-332	3	33
3 <sup>14</sup>	Lattice location of diffused Zn atoms in GaAs and InP single crystals. <i>Journal of Applied Physics</i> , <b>1991</b> , 69, 2998-3006	2.5	33
3 <sup>13</sup>	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 112105	3-4	32
3 <sup>12</sup>	Metal-insulator transition by isovalent anion substitution in Ga <sub>1-x</sub> MnxAs: implications to ferromagnetism. <i>Physical Review Letters</i> , <b>2008</b> , 101, 087203	7-4	32
3 <sup>11</sup>	High-temperature Hall effect in Ga <sub>1-x</sub> MnxAs. <i>Physical Review B</i> , <b>2004</b> , 69,	3-3	32
3 <sup>10</sup>	Annealing of AsGa-related defects in LT-GaAs: The role of gallium vacancies. <i>Journal of Electronic Materials</i> , <b>1993</b> , 22, 1401-1404	1.9	32
3 <sup>09</sup>	Fermi level stabilization and band edge energies in CdxZn <sub>1-x</sub> O alloys. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 233708	2.5	31
3 <sup>08</sup>	GaN <sub>1-x</sub> Bix: Extremely mismatched semiconductor alloys. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 141919	3-4	31
3 <sup>07</sup>	Temperature dependence of the band gap of ZnSe <sub>1-x</sub> Ox. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 151907	3-4	31
3 <sup>06</sup>	Characterization of low-temperature molecular-beam-epitaxy grown GaBiAs layers. <i>Semiconductor Science and Technology</i> , <b>2007</b> , 22, 819-823	1.8	31
3 <sup>05</sup>	Dislocation density reduction by isoelectronic impurities in semiconductors. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 2009-2011	3-4	31
3 <sup>04</sup>	Growth of Thick InN by Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 743, L4.10.1		30
3 <sup>03</sup>	Band anticrossing in group II-Ox <sub>1-x</sub> highly mismatched alloys: Cd <sub>1-x</sub> MnyOxTe <sub>1-x</sub> quaternaries synthesized by O ion implantation. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 1571-1573	3-4	30
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290	Origin of n-type conductivity of low-temperature grown InP. <i>Journal of Applied Physics</i> , <b>1994</b> , 76, 600-602.5	2.5	27
289	Band anticrossing in dilute nitrides. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, S3355-S3372	1.8	26
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